



ATP301 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Avalanche resistance guarantee.
- 10V drive.
- Halogen free compliance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-100	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-28	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycles≤1%	-112	A
Allowable Power Dissipation	P _D	T _c =25°C	70	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		54	mJ
Avalanche Current *2	I _{AV}		-28	A

Note : *1 V_{DD}=-30V, L=100μH, I_{AV}=-28A

*2 L≤100μH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0V	-100			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-2.0		-3.5	V

Marking : ATP301

Continued on next page.

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ATP301

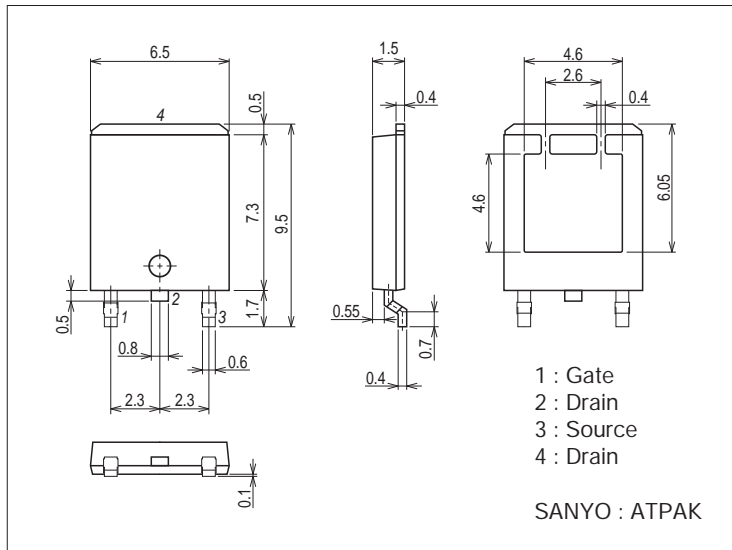
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-14A$		32		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=-14A, V_{GS}=-10V$		57	75	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-20V, f=1MHz$		4000		pF
Output Capacitance	C_{oss}	$V_{DS}=-20V, f=1MHz$		270		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-20V, f=1MHz$		150		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		32		ns
Rise Time	t_r	See specified Test Circuit.		130		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		330		ns
Fall Time	t_f	See specified Test Circuit.		190		ns
Total Gate Charge	Q_g	$V_{DS}=-60V, V_{GS}=-10V, I_D=-28A$		73		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-60V, V_{GS}=-10V, I_D=-28A$		16		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-60V, V_{GS}=-10V, I_D=-28A$		14		nC
Diode Forward Voltage	V_{SD}	$I_S=-28A, V_{GS}=0V$		-1.0	-1.5	V

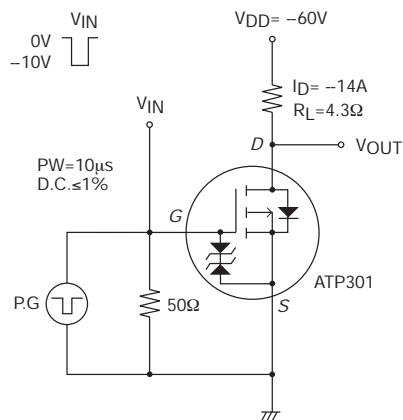
Package Dimensions

unit : mm (typ)

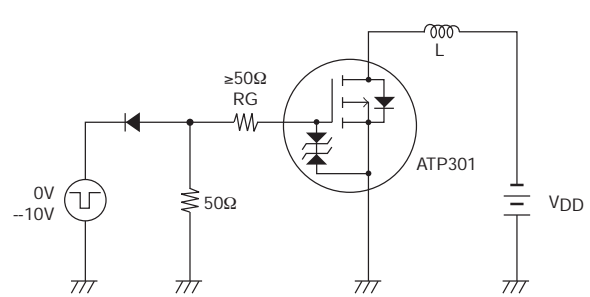
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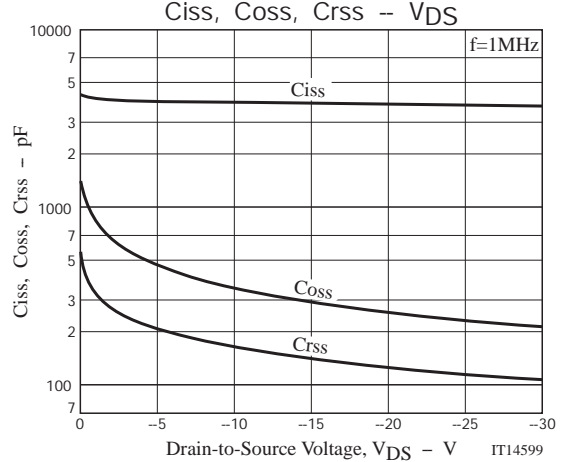
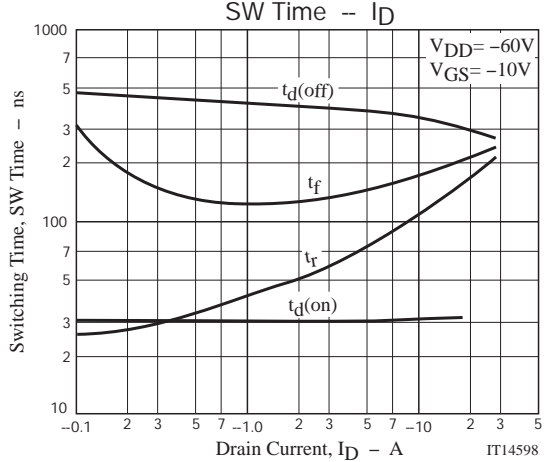
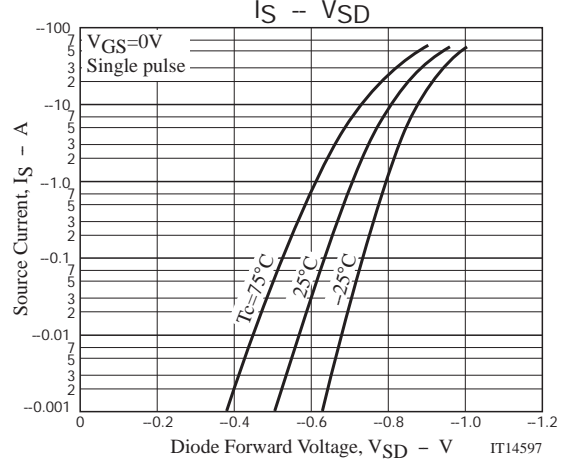
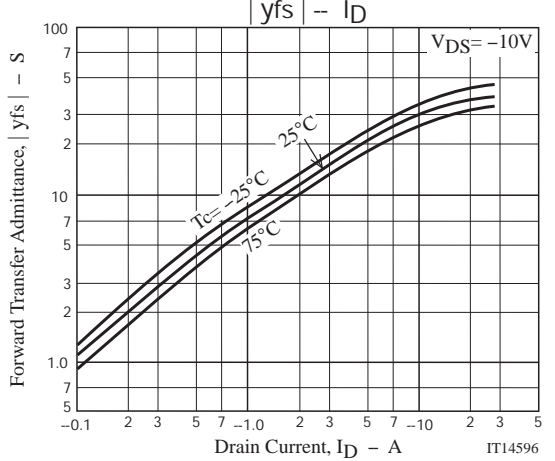
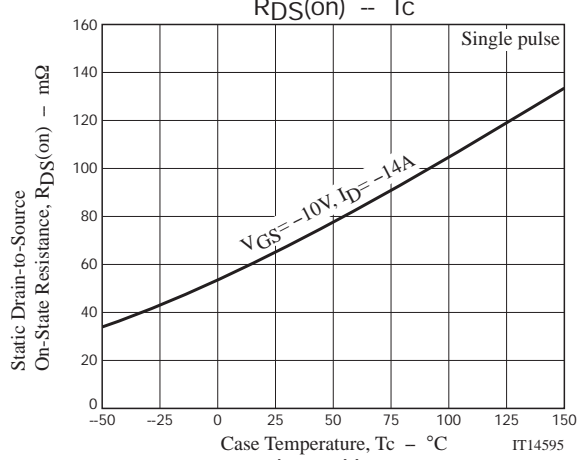
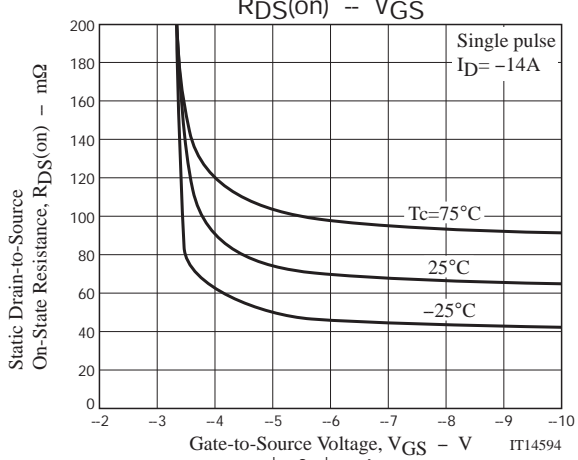
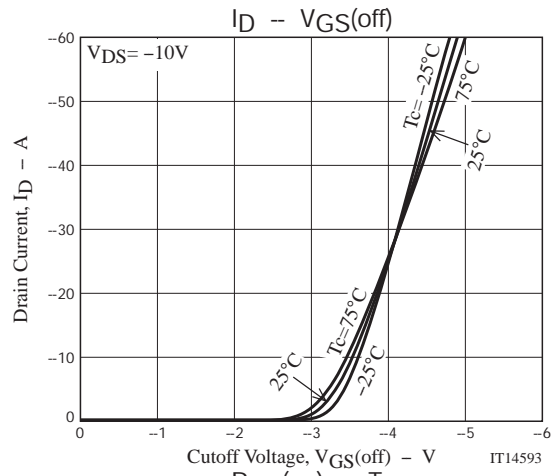
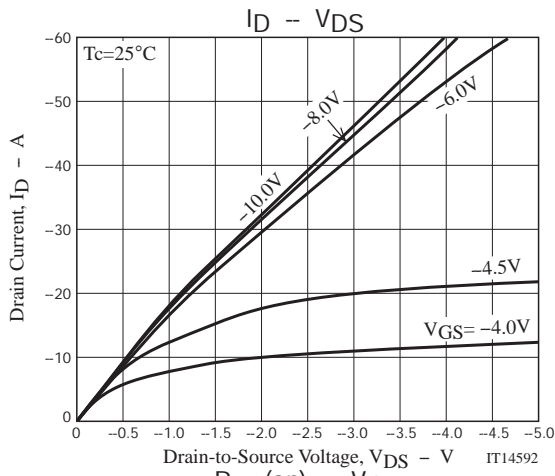


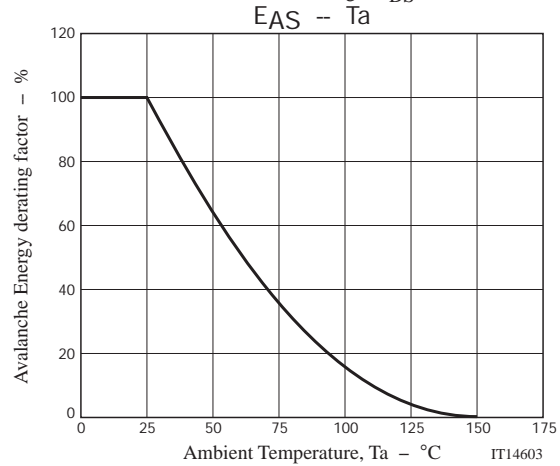
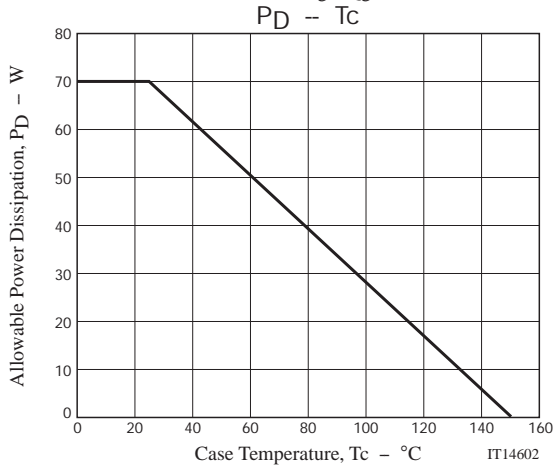
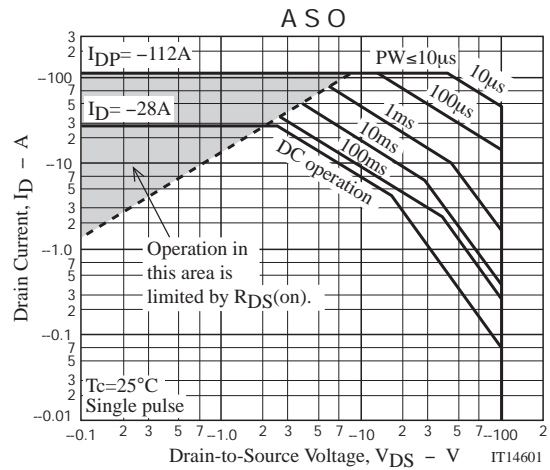
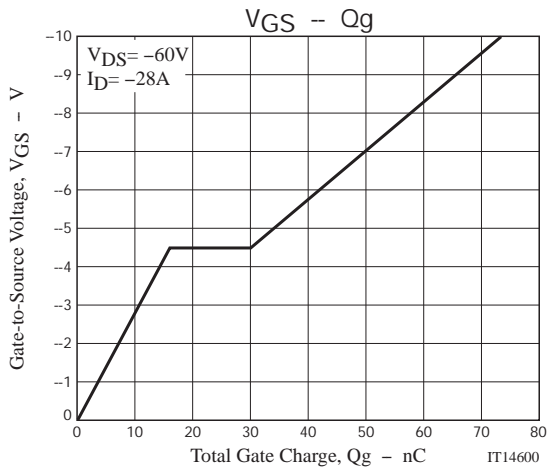
Switching Time Test Circuit



Avalanche Resistance Test Circuit







Note on usage : Since the ATP301 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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